

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 2307** is Designed for General Purpose Class C Power Amplifier Applications up to 3000 MHz.

FEATURES:

- $P_G = 9.5$ dB min. at 7 W / 2300 MHz
- Hermetic Microstrip Package
- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|---------------|---------------------------------|
| I_C | 1.2 A |
| V_{CC} | 26 V |
| P_{DISS} | 21.4 W @ $T_C \leq 50^\circ C$ |
| T_J | $-65^\circ C$ to $+200^\circ C$ |
| T_{STG} | $-65^\circ C$ to $+200^\circ C$ |
| θ_{JC} | $7.0^\circ C/W$ |

PACKAGE STYLE .250 2L FLG

| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .028 / 0.71 | .032 / 0.81 |
| B | .740 / 18.80 | |
| C | .245 / 6.22 | .255 / 6.48 |
| D | .128 / 3.25 | .132 / 3.35 |
| E | | .125 / 3.18 |
| F | .110 / 2.79 | .117 / 2.97 |
| G | | .117 / 2.97 |
| H | .560 / 14.22 | .570 / 14.48 |
| I | .790 / 20.07 | .810 / 20.57 |
| J | .225 / 5.72 | .235 / 5.97 |
| K | .165 / 4.19 | .185 / 4.70 |
| L | .003 / 0.08 | .007 / 0.18 |
| M | .058 / 1.47 | .068 / 1.73 |
| N | .119 / 3.02 | .135 / 3.43 |
| P | .149 / 3.78 | .187 / 4.75 |

ORDER CODE: ASI10536

CHARACTERISTICS $T_C = 25^\circ C$

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|------------|---|---------|---------|---------|-------|
| BV_{CBO} | $I_C = 1$ mA | 44 | | | V |
| BV_{CER} | $I_C = 5$ mA $R_{BE} = 10 \Omega$ | 44 | | | V |
| BV_{EBO} | $I_E = 1$ mA | 3.5 | | | V |
| I_{CBO} | $V_{CB} = 22$ V | | | 0.5 | mA |
| h_{FE} | $V_{CE} = 5.0$ V $I_C = 500$ mA | 30 | | 300 | --- |
| C_{ob} | $V_{CB} = 22$ V $f = 1.0$ MHz | | | 8.5 | pF |
| P_G | $V_{CC} = 22$ V $P_{OUT} = 7.0$ W $f = 2.3$ GHz | 9.5 | | | dB |
| η_C | | 33 | | | % |